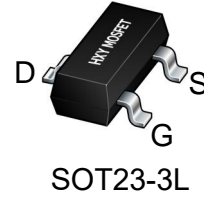




## Description

The HXY3415MI uses advanced trench technology to provide excellent  $R_{DS(ON)}$ , low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.

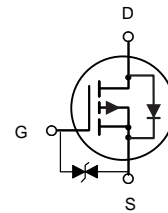


## General Features

$V_{DS} = -20V$   $I_D = -4.1A$   
 $R_{DS(ON)} < 45m\Omega @ V_{GS} = -4.5V$   
ESD Rating: 1500V HBM

## Application

Battery protection  
Load switch  
Uninterruptible power supply



P-Channel MOSFET

## Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HXY3415MI	SOT23-3L		3000

## Absolute Maximum Ratings ( $T_A=25^{\circ}C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	$\pm 10$	V
$I_D$	Drain Current-Continuous	-4.1	A
$I_{DM}$	Drain Current-Pulsed (Note 1)	-30	A
$P_D$	Maximum Power Dissipation	1.4	W
$T_J, T_{STG}$	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}C$
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 2)	89.3	$^{\circ}C/W$



**Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)**

Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-20V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±10V, V <sub>DS</sub> =0V	-	-	±10	μA
<b>On Characteristics (Note 3)</b>						
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250μA	-0.35	-0.55	-0.9	V
Drain-Source On-State Resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-4A	-	34	45	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-4A	-	44	60	mΩ
Forward Transconductance	g <sub>FS</sub>	V <sub>DS</sub> =-5V, I <sub>D</sub> =-4A	8	-	-	S
<b>Dynamic Characteristics (Note4)</b>						
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-10V, V <sub>GS</sub> =0V, F=1.0MHz	-	950	-	PF
Output Capacitance	C <sub>oss</sub>		-	165	-	PF
Reverse Transfer Capacitance	C <sub>rss</sub>		-	120	-	PF
<b>Switching Characteristics (Note 4)</b>						
Turn-on Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-10V, R <sub>L</sub> =2.5Ω V <sub>GS</sub> =-4.5V, R <sub>GEN</sub> =3Ω	-	12		nS
Turn-on Rise Time	t <sub>r</sub>		-	10		nS
Turn-Off Delay Time	t <sub>d(off)</sub>		-	19		nS
Turn-Off Fall Time	t <sub>f</sub>		-	25		nS
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-4A, V <sub>GS</sub> =-4.5V	-	12		nC
Gate-Source Charge	Q <sub>gs</sub>		-	1.4	-	nC
Gate-Drain Charge	Q <sub>gd</sub>		-	3.6	-	nC
<b>Drain-Source Diode Characteristics</b>						
Diode Forward Voltage (Note 3)	V <sub>SD</sub>	V <sub>GS</sub> =0V, I <sub>S</sub> =-4A	-	-	-1.2	V
Diode Forward Current (Note 2)	I <sub>S</sub>		-	-	-4	A

**Notes:**

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
4. Guaranteed by design, not subject to production



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

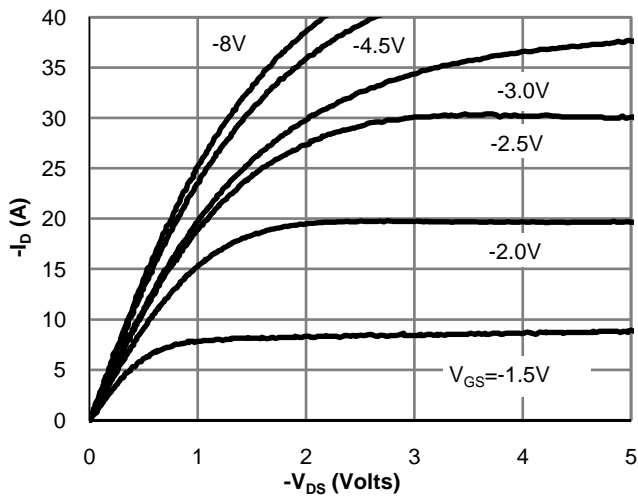


Fig 1: On-Region Characteristics (Note E)

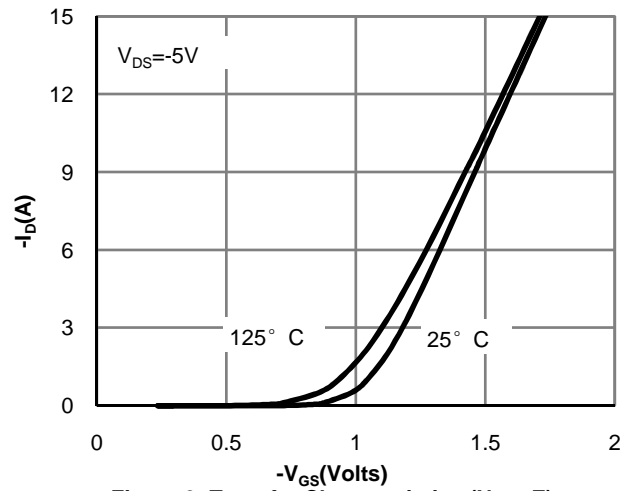


Figure 2: Transfer Characteristics (Note E)

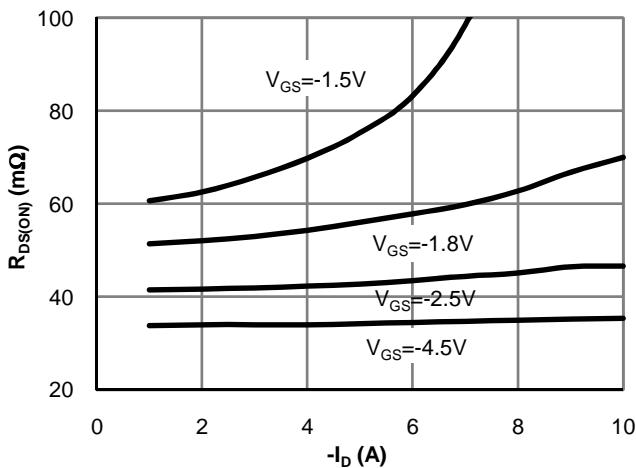


Figure 3: On-Resistance vs. Drain Current and Gate Voltage (Note E)

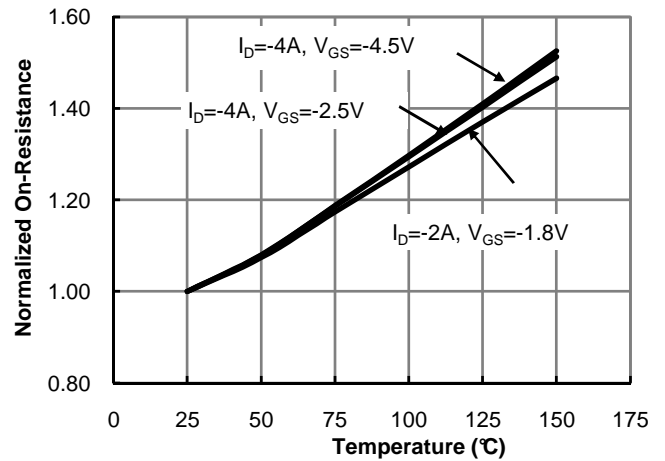


Figure 4: On-Resistance vs. Junction Temperature (Note E)

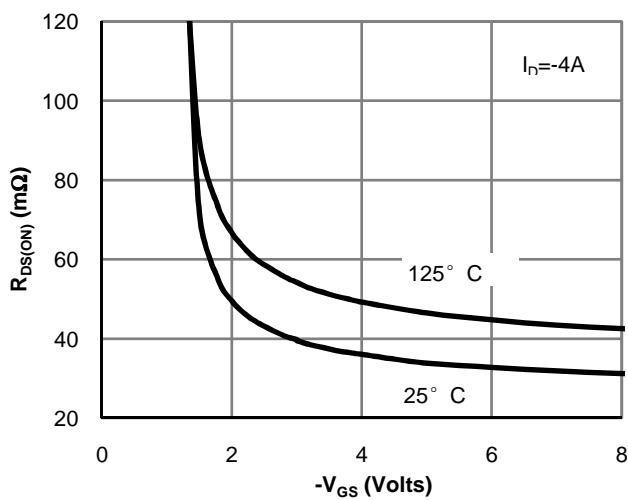


Figure 5: On-Resistance vs. Gate-Source Voltage (Note E)

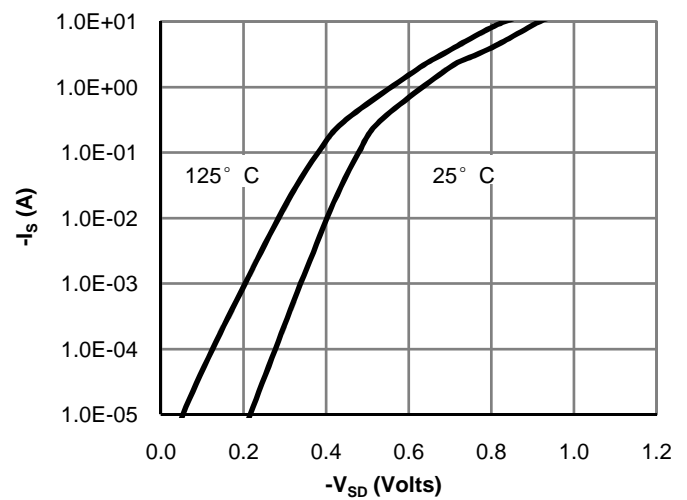


Figure 6: Body-Diode Characteristics (Note E)



### TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

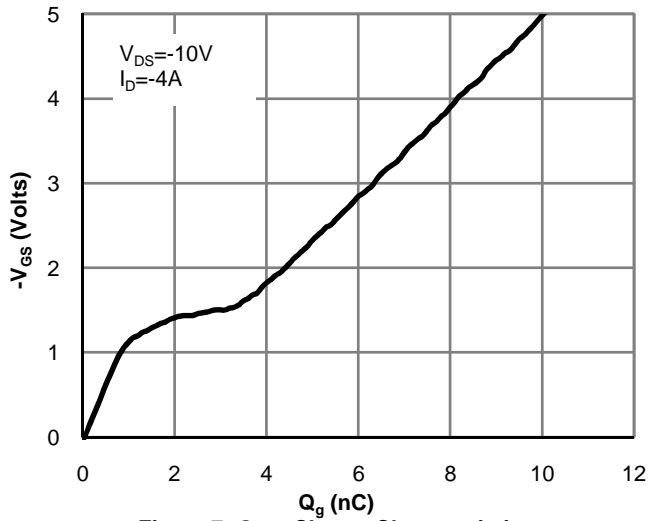


Figure 7: Gate-Charge Characteristics

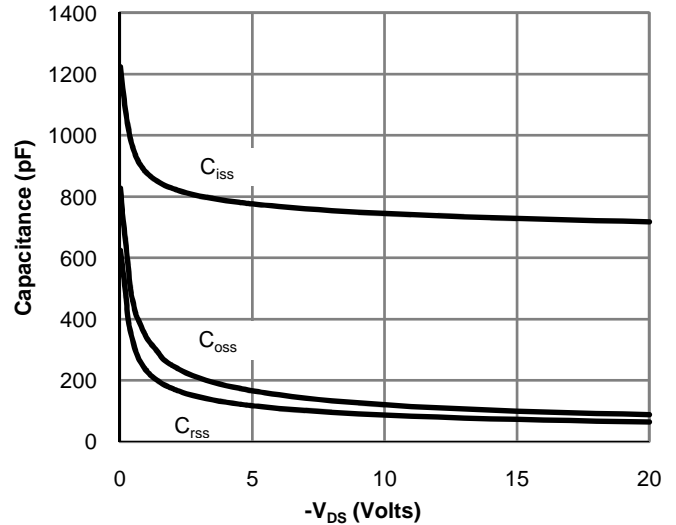


Figure 8: Capacitance Characteristics

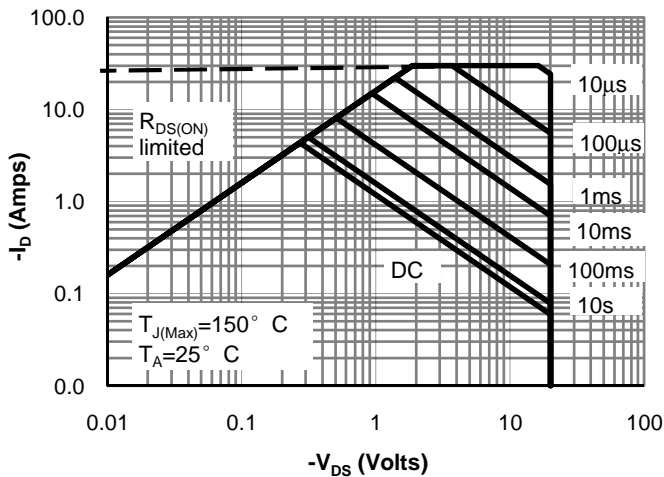


Figure 9: Maximum Forward Biased Safe Operating Area (Note F)

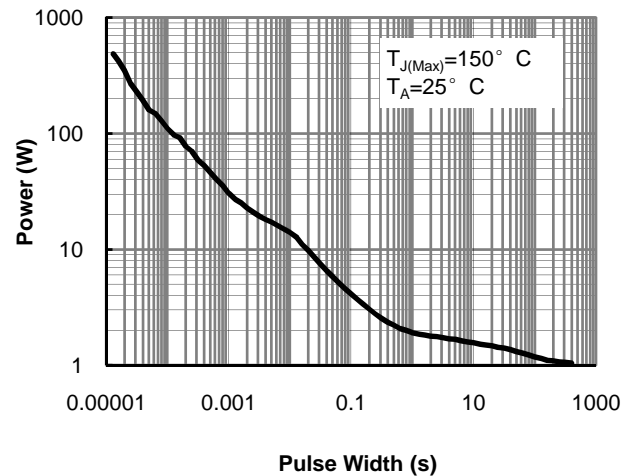


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note F)

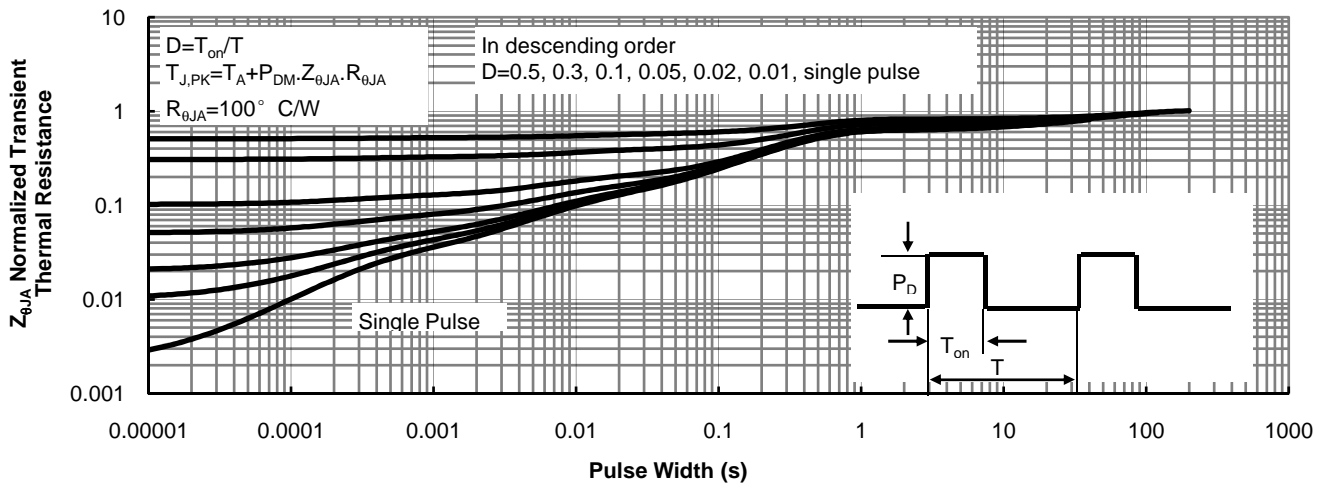
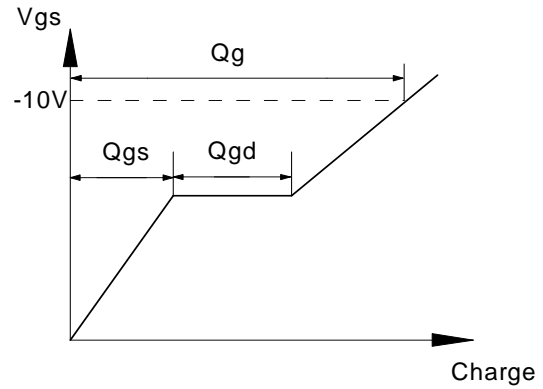
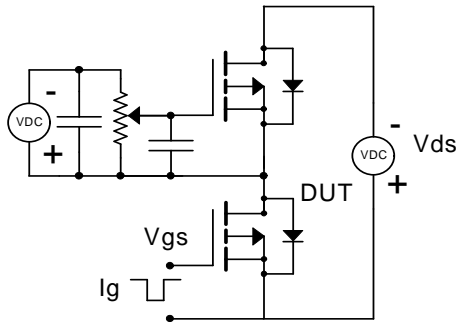


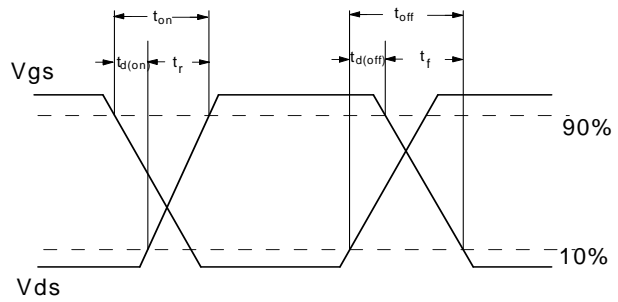
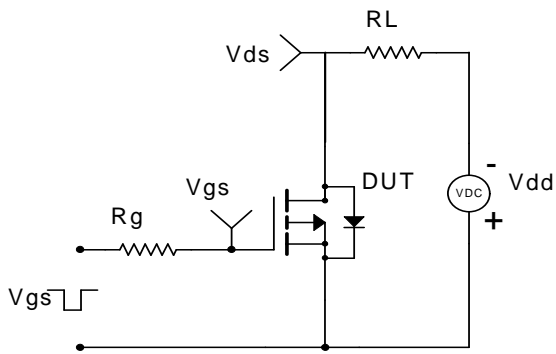
Figure 11: Normalized Maximum Transient Thermal Impedance (Note F)



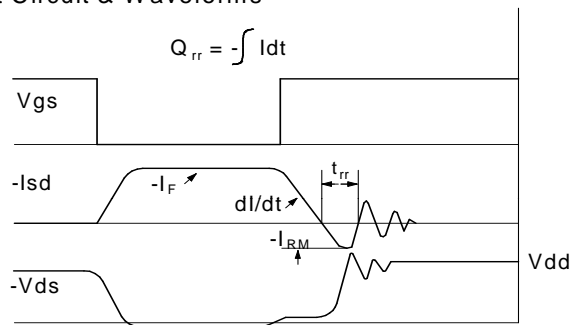
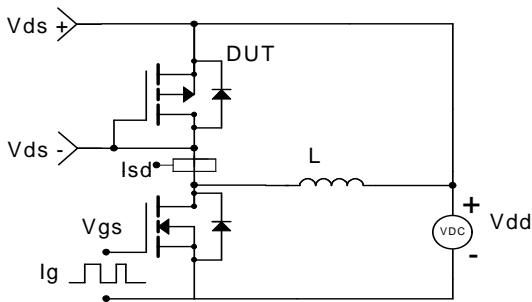
### Gate Charge Test Circuit & Waveform



### Resistive Switching Test Circuit & Waveforms

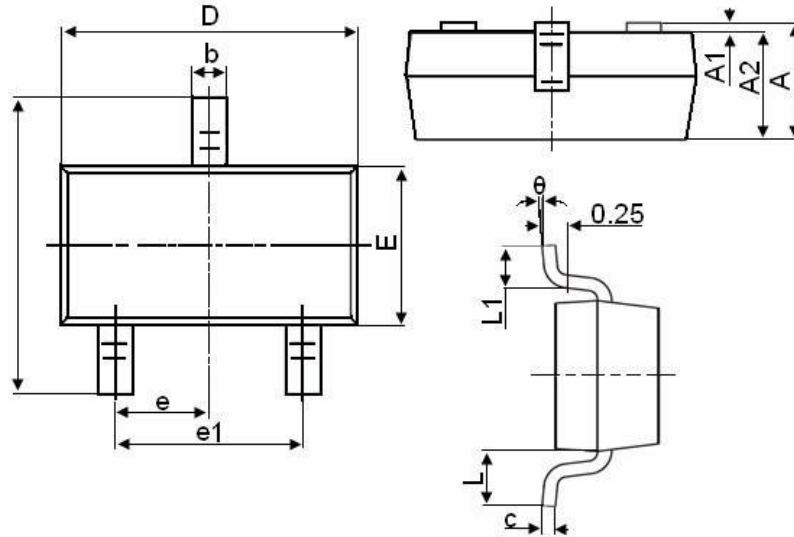


### Diode Recovery Test Circuit & Waveforms





**SOT23-3L Package Information**



Symbol	Dimensions in Millimeters	
	MIN.	MAX.
A	1.050	1.250
A1	0.000	0.100
A2	1.050	1.150
b	0.300	0.500
c	0.100	0.200
D	2.800	3.000
E	1.500	1.700
E1	2.650	2.950
e	0.950TYP	
e1	1.800	2.000
L	0.550REF	
L1	0.300	0.600
$\theta$	0°	8°



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